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REQUEST FOR CONTINUED EXAMINATION (RCE) TRANSMITTAL

Address to:
Commissioner for Patents
Box RCE
Washington, DC 20231

Application Number	09/902,672 ✓
Filing Date	July 12, 2001
First Named Inventor	M. Funabashi
Art Unit	2825
Examiner Name	L. Malsawma
Attorney Docket Number	843.37558VX2

This is a Request for Continued Examination (RCE) under 37 C.F.R. § 1.114 of the above-identified application.

Request for Continued Examination (RCE) practice under 37 CFR 1.114 does not apply to any utility or plant application filed prior to June 8, 1995, or to any design application. See Instruction Sheet for RCEs (not to be submitted to the USPTO) on page 2.

1. **Submission** required under 37 C.F.R. § 1.114

- a. ☐ Previously submitted
- i. ☐ Consider the amendment(s)/reply under 37 C.F.R. § 1.116 previously filed on ____
(Any unentered amendment(s) referred to above will be entered).
- ii. ☐ Consider the arguments in the Appeal Brief or Reply Brief previously filed on ____
- iii. ☐ Other ____
- b. ☒ Enclosed
- i. ☒ Amendment/Reply
- ii. ☐ Affidavit(s)/Declaration(s)
- iii. ☐ Information Disclosure Statement (IDS)
- iv. ☐ Other ____

2. **Miscellaneous**

- a. ☐ Suspension of action on the above-identified application is requested under 37 C.F.R. § 1.103(c) for a period of ____ months. (Period of suspension shall not exceed 3 months; Fee under 37 C.F.R. § 1.17(i) required)
- b. ☐ Other ____

3. **Fees** The RCE fee under 37 C.F.R. § 1.17 (e) is required by 37 C.F.R. § 1.114 when RCE is filed.

- a. ☒ The Director is hereby authorized to charge the following fees, or credit any overpayments, to Deposit Account No. **01-2135 (Case No. 843.37558VX2)**
- i. ☐ RCE fee required under 37 C.F.R. § 1.17 (e)
- ii. ☐ Extension of time fee (37 C.F.R. §§ 1.136 and 1.17)
- iii. ☐ Other ____
- b. ☐ Check in the amount of \$ ____ enclosed
- c. ☒ Payment by credit card (Form PTO-2038 enclosed)

WARNING: Information on this form may become public. Credit card information should not be included on this form. Provide credit card information and authorization on PTO-2038.

SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT REQUIRED

Name (Print/Type)	William I. Solomon	Registration No. (Attorney/Agent)	28,565
Signature	<i>William I. Solomon</i>	Date	May 16, 2003

CERTIFICATE OF MAILING OR TRANSMISSION

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner For Patents, Box RCE, Washington, DC 20231, or facsimile transmitted to the U.S. Patent and Trademark Office on the date shown below:

Name (Print/Type)	William I. Solomon	Date	May 16, 2003
Signature			

Burden Hour Statement: This form is estimated to take 0.2 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND Fees and Completed Forms to the following address: Assistant Commissioner for Patents, Box RCE, Washington, DC 20231.

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

843.37558VX2

*Attachment #14/D
Liggett
5/20/03*

Applicant(s): FUNABASHI
Serial No.: 09/902,672 ✓
Filed: July 12, 2001
For: METHOD OF MANUFACTURING A SEMICONDUCTOR
INTEGRATED CIRCUIT DEVICE
Group: 2825
Examiner: L. Malsawma

SUBMISSION UNDER 37 CFR § 1.114
(AMENDMENT)

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Filed concurrently with the Request for Continued Examination (RCE)
Transmittal for the above-identified application, and as the necessary Submission
therefor, please amend the above-identified application as follows.

May 16, 2003

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IN THE CLAIMS

Please amend the claims presently in the application as follows:

- DI
17. (Amended) A method of manufacturing a semiconductor integrated circuit device, comprising the steps of:
- (a) providing a silicon wafer covered with an insulating film whose main surface is mainly formed of silicon oxide;

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